

PN4250A



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage 60		V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage 5.0		V
Ic	Collector Current - Continuous 500		mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range -55 to +150 °C		°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN4250A	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

Voint Voin	lector-Emitter Breakdown tage* lector-Emitter Breakdown tage* lector-Base Breakdown Voltage itter-Base Breakdown Voltage lector-Cutoff Current itter-Cutoff Current	$I_{C} = 5.0 \text{ mA}, I_{B} = 0$ $I_{C} = 10 \mu\text{A}, I_{B} = 0$ $I_{C} = 10 \mu\text{A}, I_{E} = 0$ $I_{E} = 10 \mu\text{A}, I_{C} = 0$ $V_{CB} = 50 \text{ V}, I_{C} = 0$ $V_{CB} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	60 60 60 5.0	10 20	V V V V NA nA
V(BR)CEO Col Volvol V(BR)CES Col Volvol V(BR)CBO Col V(BR)CBO Em ICBO Col I _{EBO} Em ON CHARACT hFE DC VCE(sat) Col	lector-Emitter Breakdown tage* lector-Emitter Breakdown tage* lector-Base Breakdown Voltage itter-Base Breakdown Voltage lector-Cutoff Current itter-Cutoff Current ERISTICS* Current Gain	I_C = 10 μA, I_B = 0 I_C = 10 μA, I_E = 0 I_E = 10 μA, I_C = 0 V_{CB} = 50 V, I_C = 0 V_{CB} = 3.0 V, I_C = 100 μA	60 60 5.0	20	V V V nA
Vol V(BR)CBO Col V(BR)EBO Em ICBO Col IEBO Em ON CHARACT hFE DC VCE(sat) Col	tage* lector-Base Breakdown Voltage itter-Base Breakdown Voltage lector-Cutoff Current itter-Cutoff Current ERISTICS* Current Gain	$I_{C} = 10 \ \mu\text{A}, \ I_{E} = 0$ $I_{E} = 10 \ \mu\text{A}, \ I_{C} = 0$ $V_{CB} = 50 \ V, \ I_{C} = 0$ $V_{EB} = 3.0 \ V, \ I_{C} = 0$ $V_{CE} = 5.0 \ V, \ I_{C} = 100 \ \mu\text{A}$	60 5.0	20	V V nA
V(BR)EBO Em ICBO Col IEBO Em ON CHARACT hFE DC VCE(sat) Col SMALL SIGNA	itter-Base Breakdown Voltage lector-Cutoff Current itter-Cutoff Current ERISTICS* Current Gain	I _E = 10 μA, I _C = 0 V _{CB} = 50 V, I _E = 0 V _{EB} = 3.0 V, I _C = 0 V _{CE} = 5.0 V, I _C = 100 μA	5.0	20	V nA
ICBO Col I _{EBO} Em ON CHARACT hFE DC VCE(sat) Col SMALL SIGNA	lector-Cutoff Current itter-Cutoff Current ERISTICS* Current Gain	V _{CB} = 50 V, I _E = 0 V _{EB} = 3.0 V, I _C = 0 V _{CE} = 5.0 V, I _C = 100 μA		20	nA
ON CHARACT hFE DC VCE(sat) Col SMALL SIGNA	TERISTICS* Current Gain	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$ $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	250	20	
ON CHARACT hFE DC VCE(sat) Col SMALL SIGNA	ERISTICS* Current Gain	V _{CE} = 5.0 V, I _C = 100 μA	250	1 -	nA
ON CHARACT h _{FE} DC V _{CE(sat)} Col SMALL SIGNA	Current Gain		250	700	
SMALL SIGNA	lector-Emitter Saturation voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.25	V
	AL CHARACTERISTICS				<u> </u>
	put Capacitance	V _{CB} = 5.0 V, f = 1.0 MHz		6.0	pF
h _{fe} Sma	all-signal Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250	800	· ·
h _{ie} Inpu	ut Impedance	f = 1.0 kHz	6.0	20	kΩ
h _{oe} Out	put Admittance		5.0	50	μmhos
h _{re} Volt	age Feedback Ratio	1		10	x10 ⁻⁴
NF Nois	se Figure	$V_{CE} = 5.0 \text{ V}, I_{C} = 250 \mu\text{A},$ $R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz},$ $B_{W} = 150 Hz$ $V_{CE} = 5.0 \text{ V}, I_{C} = 20 \mu\text{A},$		2.0	dB dB

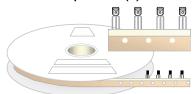
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z 2,000 D75Z **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM

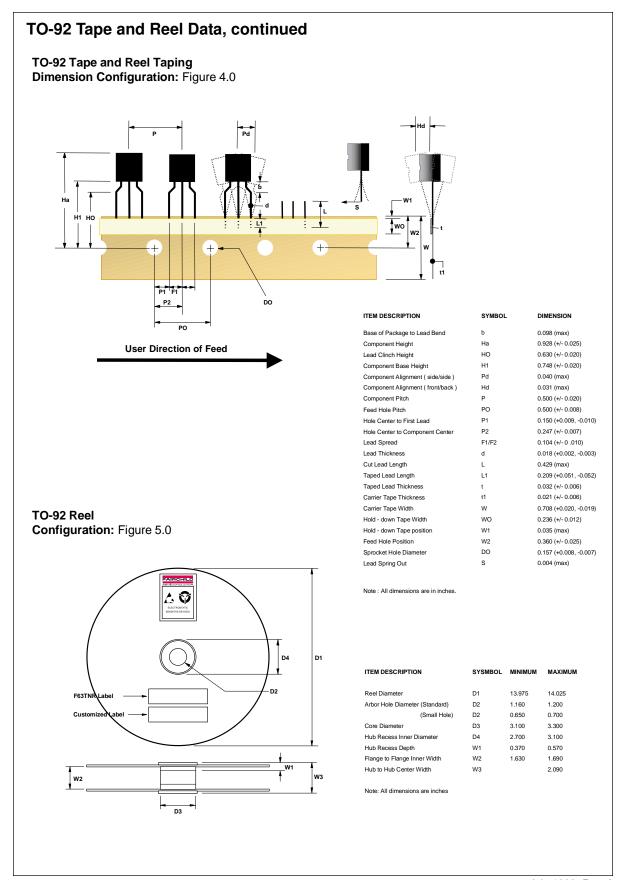
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



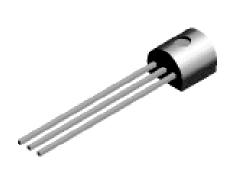


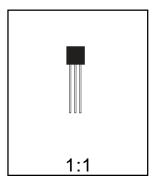


TO-92 Package Dimensions



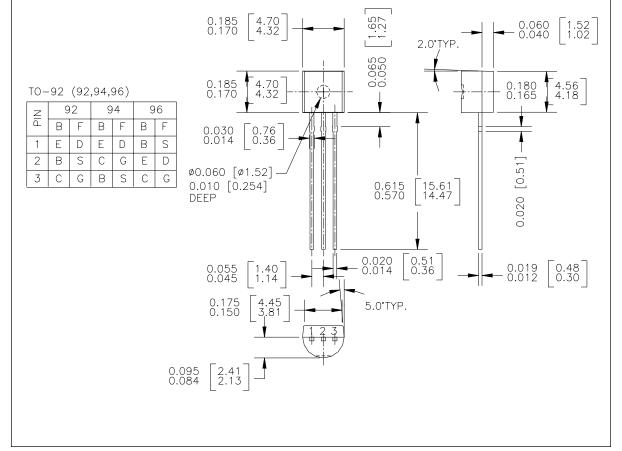
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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